

isc Silicon PNP Power Transistor

2SB979

DESCRIPTION

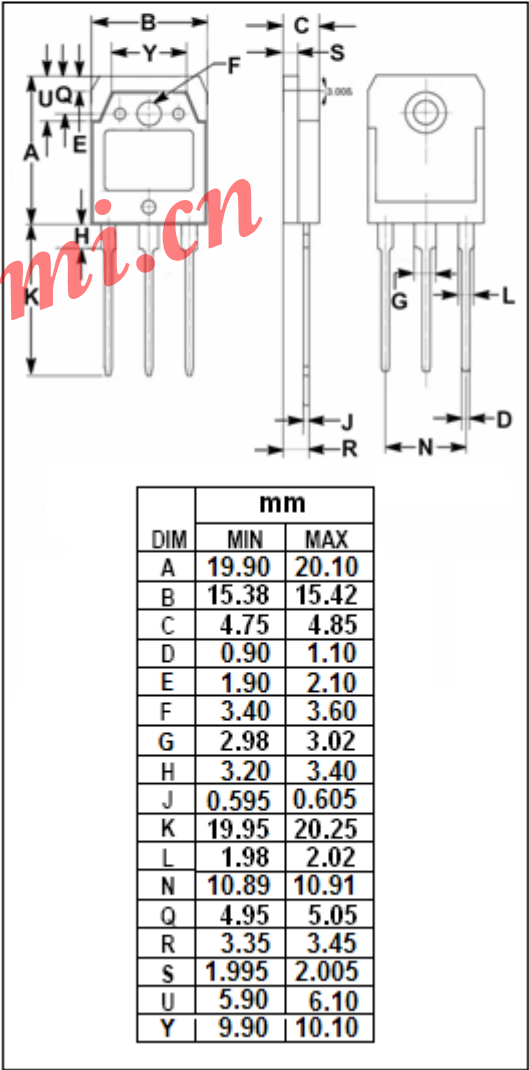
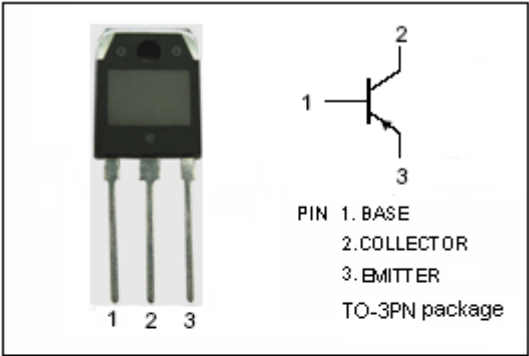
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -100V(\text{Min})$
- Good Linearity of h_{FE}
- Wide Area of Safe Operation

APPLICATIONS

- Designed for high power amplifications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-5	A
I_{CP}	Collector Current-Pulse	-8	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}\text{C}$	60	W
	Collector Power Dissipation @ $T_a=25^{\circ}\text{C}$	3	
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}\text{C}$



isc Silicon PNP Power Transistor**2SB979****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -3A; I_B = -0.3A$			-2.0	V
$V_{BE(on)}$	Base -Emitter On Voltage	$I_C = -3A; V_{CE} = -5V$			-1.8	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -100V; I_E = 0$			-50	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -3V; I_C = 0$			-50	μA
h_{FE-1}	DC Current Gain	$I_C = -20mA; V_{CE} = -5V$	20			
h_{FE-2}	DC Current Gain	$I_C = -1A; V_{CE} = -5V$	60		200	
h_{FE-3}	DC Current Gain	$I_C = -3A; V_{CE} = -5V$	20			
f_T	Current-Gain—Bandwidth Product	$I_C = -0.5A; V_{CE} = -5V; f = 1MHz$		20		MHz

◆ **h_{FE-2} Classifications**

Q	S	P
60-120	80-160	100-200